

Docket No. 240669US2/hc



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Yukio TANIGUCHI, et al.

SERIAL NO: 10/624,555

GAU:

FILED: July 23, 2003

EXAMINER:

FOR: CRYSTALLIZATION APPARATUS, CRYSTALLIZATION METHOD, THIN FILM TRANSISTOR AND DISPLAY APPARATUS

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☐ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check or credit card payment form is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check or credit card payment is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

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DOCKET NO.: 240669US2/hgc

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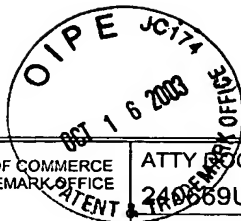
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FILM TRANSISTOR AND DISPLAY APPARATUS

STATEMENT OF RELEVANCY

Reference AZ on Form 1449:

Fig. 4 illustrates a phenomenon wherein a laser beam undergoes phase modulation at the shifting portion of a phase shift mask, thereby inclining the wavefront.



Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY Docket NO. 240669US2		SERIAL NO. 10/624,555	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Yukio TANIGUCHI, et al.			
				FILING DATE July 23, 2003		GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AA						
	AB						
	AC						
	AD						
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FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
	AO						
	AP						
	AQ						
	AR						
	AS						
	AT						
	AU						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
	AV	W. YEH, et al., Jpn. J. Appl. Phys., vol. 41, Part 1, no. 4A, pages 1909-1914, "PROPOSED SAMPLE STRUCTURE FOR MARKED ENLARGEMENT OF EXCIMER-LASER-INDUCED LATERAL GRAIN GROWTH IN Si THIN FILMS", April 2002					
	AW	M. NAKATA, et al., Jpn. J. Appl. Phys., vol. 40, Part 1, no. 5A, pages 3049-3054, "A NEW NUCLEATION-SITE-CONTROL EXCIMER-LASER-CRYSTALIZATION METHOD", May 2001					
	AX	C-H. OH, et al., Jpn. J. Appl. Phys., vol. 37, Part 2, no. 5A, pages L492 - L495, "A NOVEL PHASE-MODULATED EXCIMER-LASER CRYSTALIZATION METHOD OF SILICON THIN FILMS", May 1, 1998					
	AY	M. MATSUMURA, et al., Thin Solid Films, vol. 337, pages 123-128, "ADVANCED EXCIMER-LASER ANNEALING PROCESS FOR QUASI SINGLE-CRYSTAL SILICON THIN-FILM DEVICES", 1999					
	AZ	M. MATSUMURA, Applied Physics, vol. 71, no. 5, pages 543-547, "EXCIMER-LASER-GROWN SILICON THIN FILMS WITH ULTRALARGE GRAINS", 2002				<input type="checkbox"/> Additional References sheet(s) attached	
Examiner					Date Considered		
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							